

Fig. 1 PRIOR ART

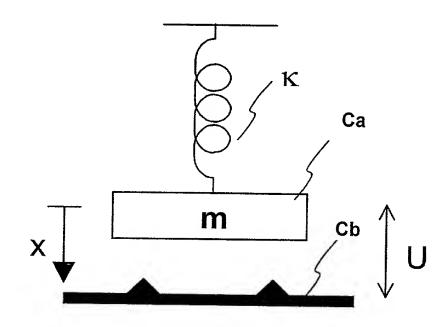


Fig. 2 PRIOR ART

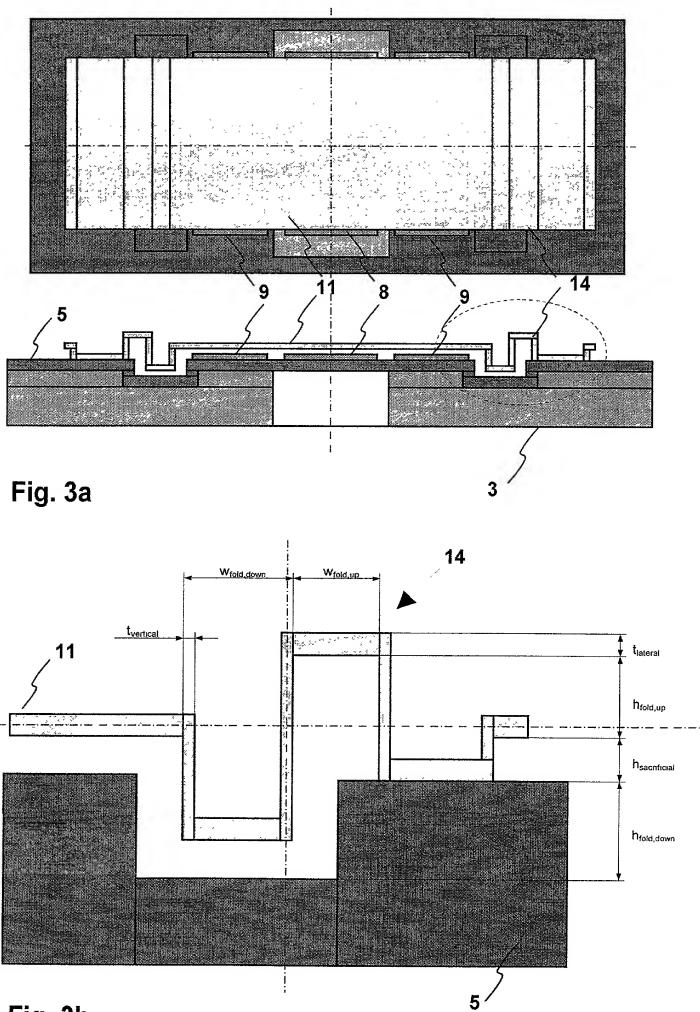


Fig. 3b

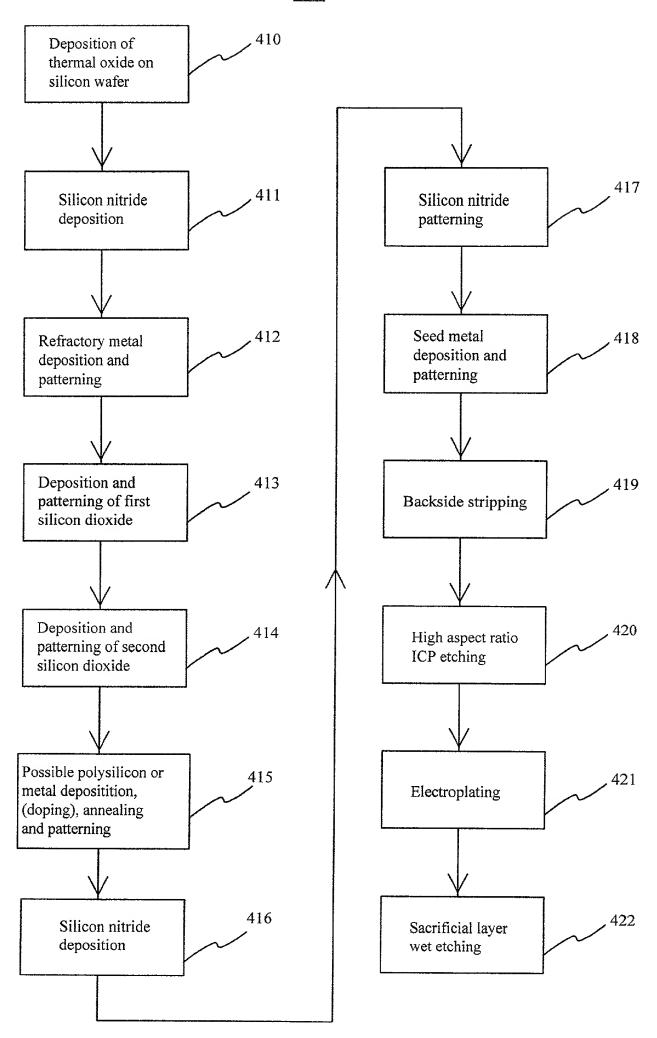
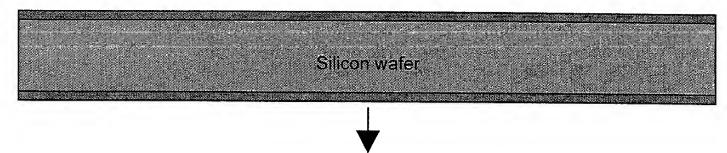
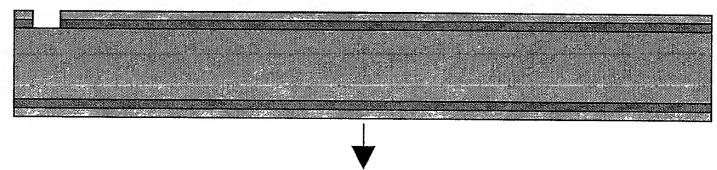


FIG. 4a

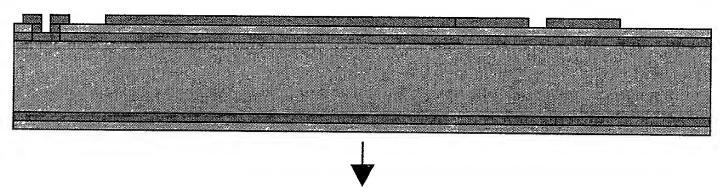
410 Thermal oxide (~1 μ m)



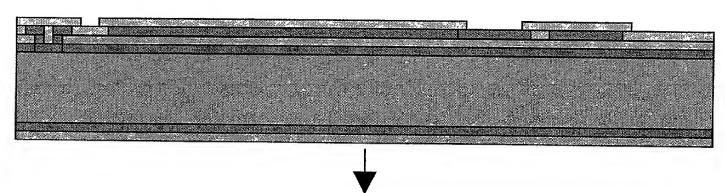
411 Silicon nitride deposition (~1 μm) and patterning



412 Refractory metal (molybdeen or tungsten) deposition and patterning



413 First silicon dioxide deposition and patterning (plasma) (0.4 - $0.5\,\mu\text{m})$



414 Second silicon dioxide deposition and patterning (plasma) (0.5 μ m)

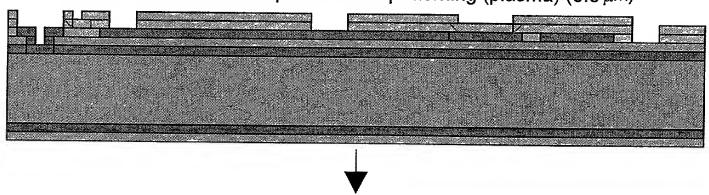
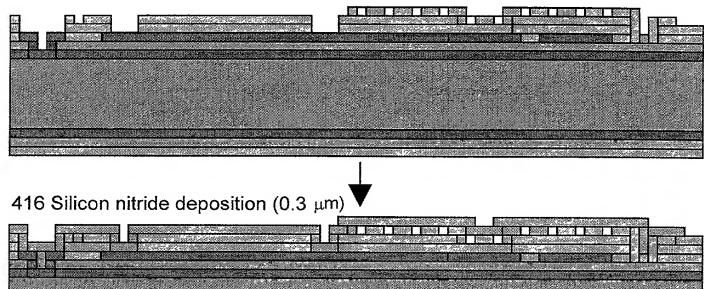
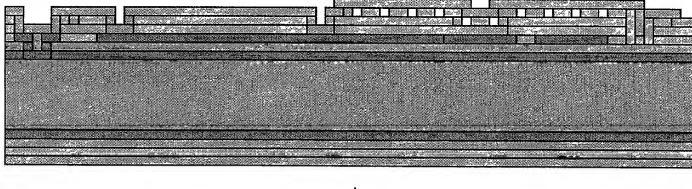


FIG. 4b

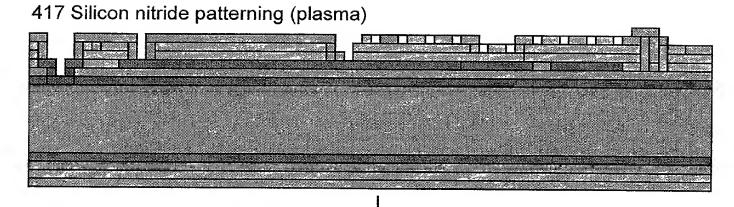


415 Polysilicon deposition (2-5 μ m), doping, annealing and patterning; (PolySi: < 5 Ω / \square ; tensile residual stress: 10 MPa)

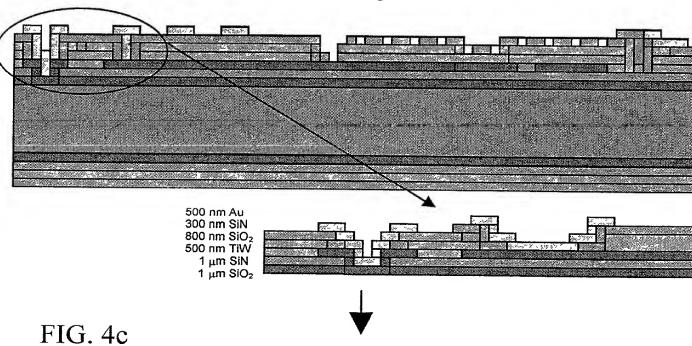








418 Seed metal deposition and patterning



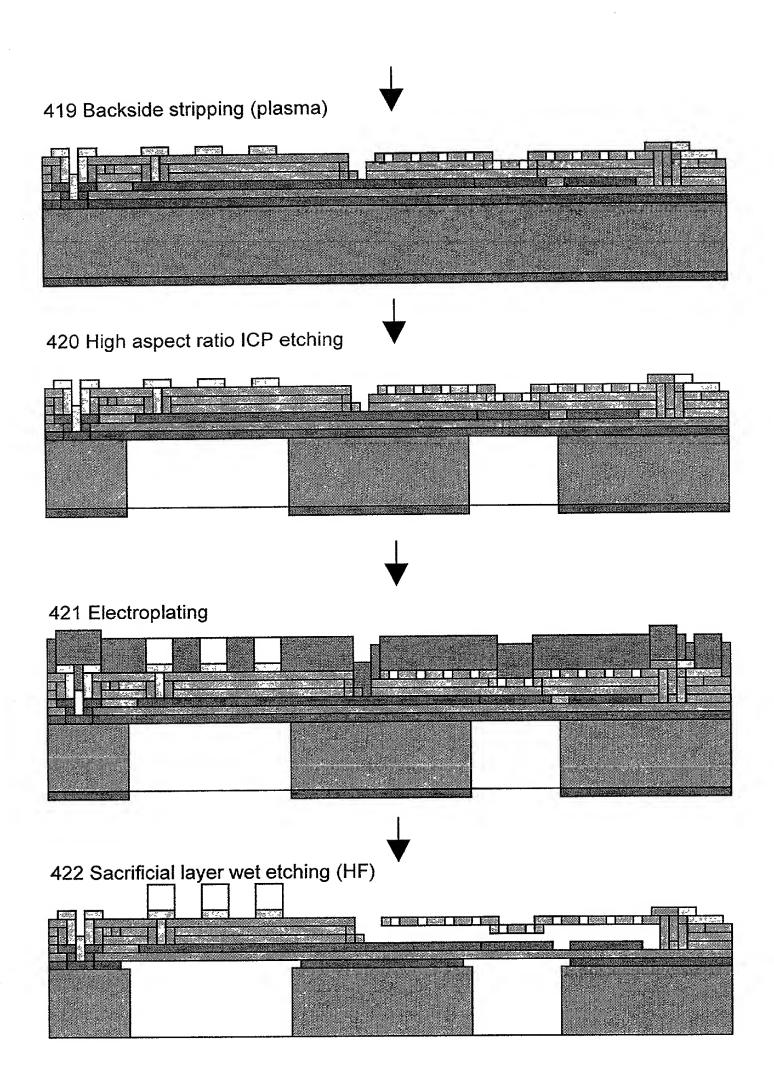


FIG. 4d

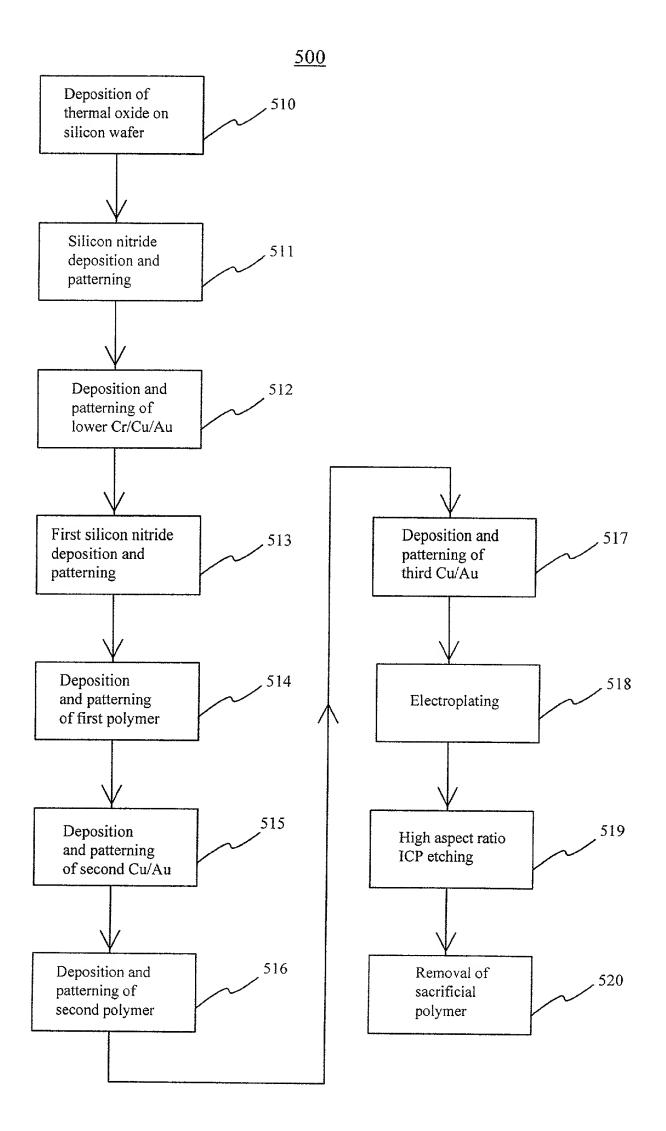
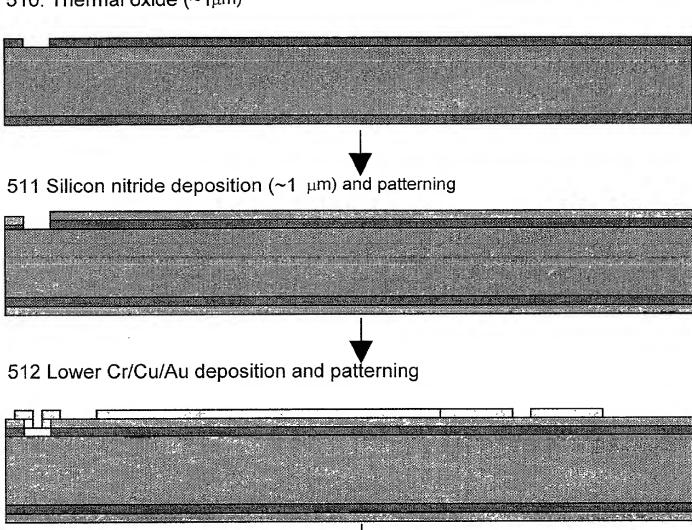
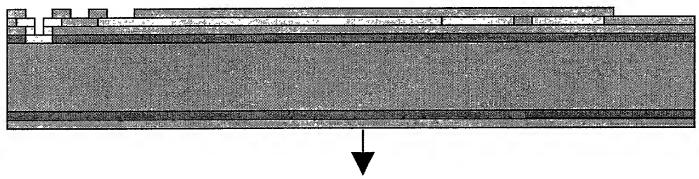


FIG. 5a

510. Thermal oxide (~1 μ m)



513 Silicon nitride deposition (0.2 - 0.3 $\,\mu\text{m}$) and patterning



514 First polymer deposition and patterning

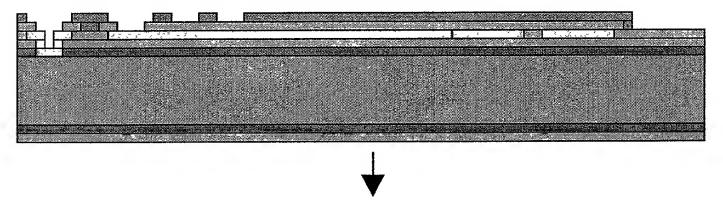
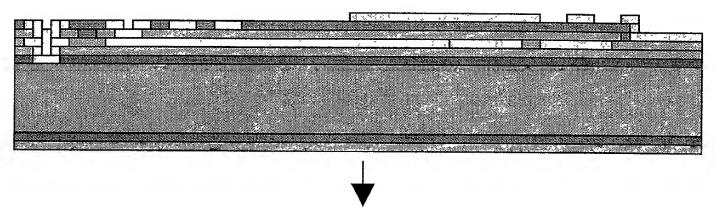


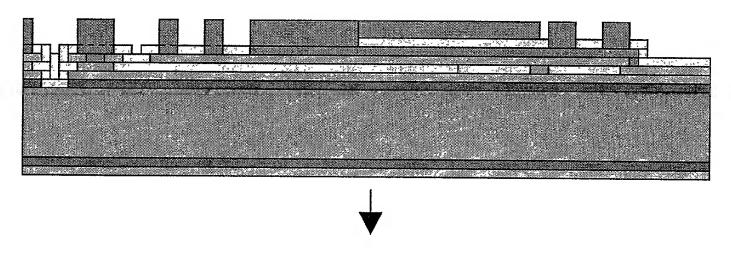
FIG. 5b



515 Second Cu/Au deposition and patterning



516 Second polymer deposition and patterning



517 Third Cu/Au deposition and patterning

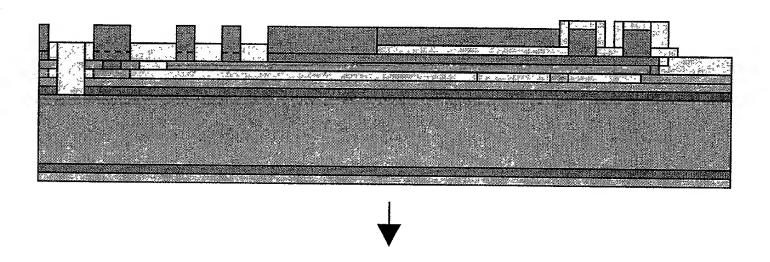


FIG. 5c

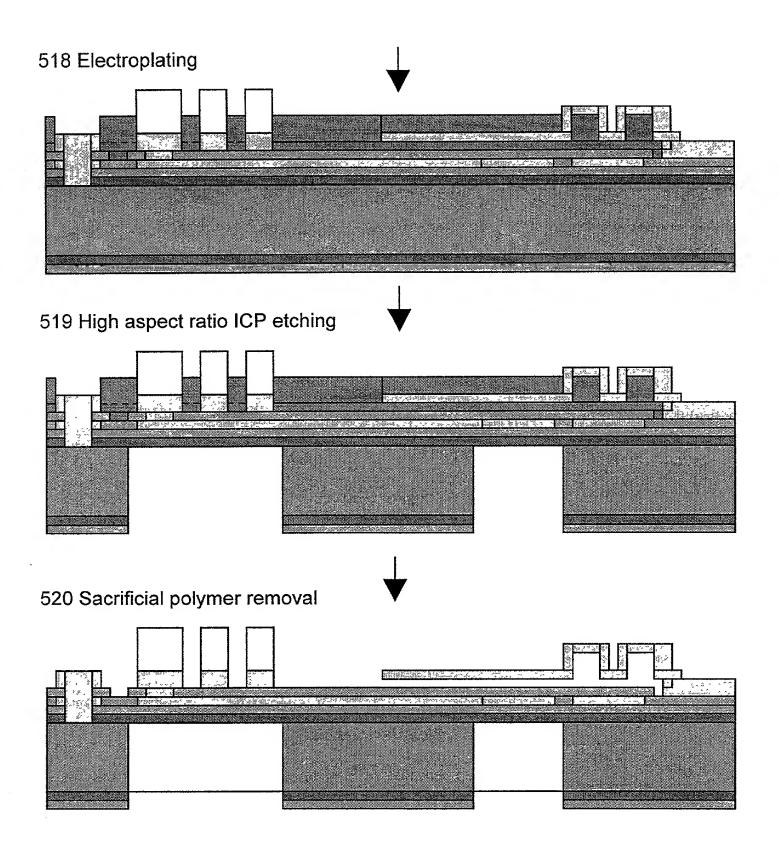


FIG. 5d

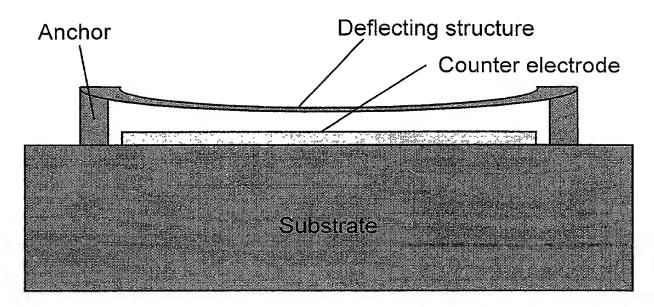


Fig. 6a PRIOR ART

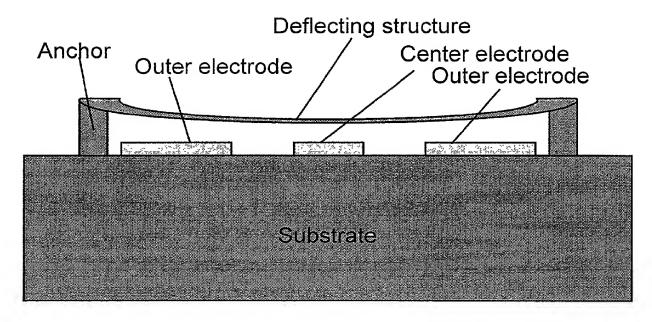


Fig. 6b

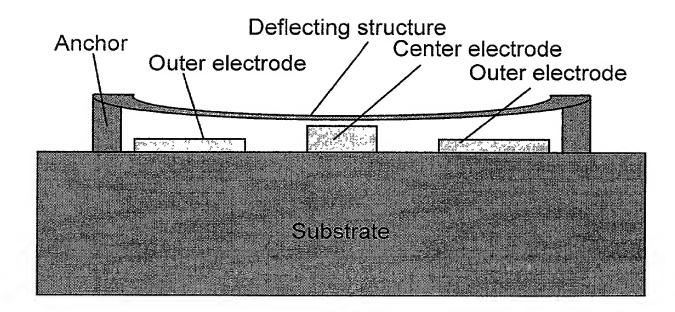


Fig. 6c

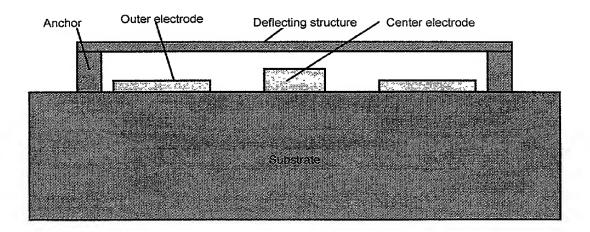


Fig. 7a

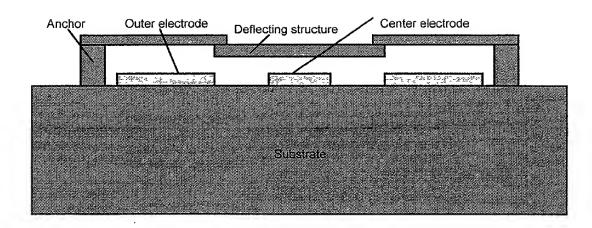


Fig. 7b

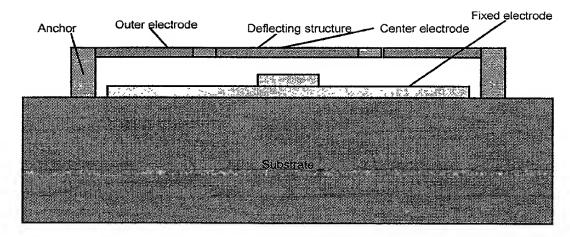


Fig. 7c

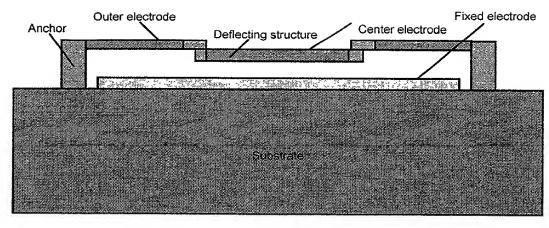
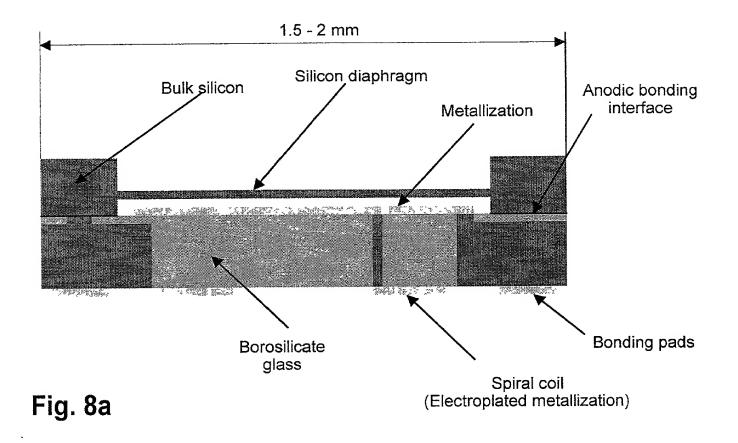


Fig. 7d



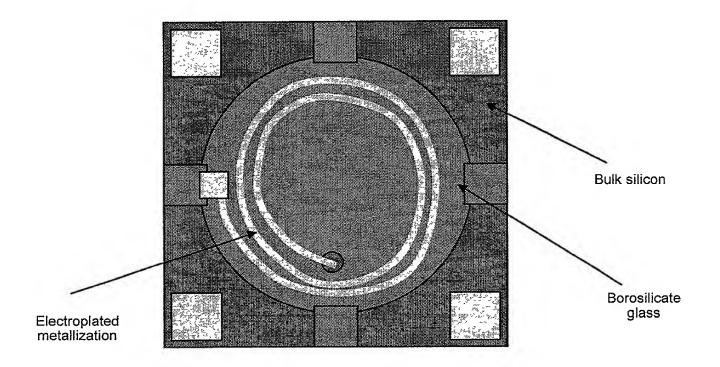


Fig. 8b

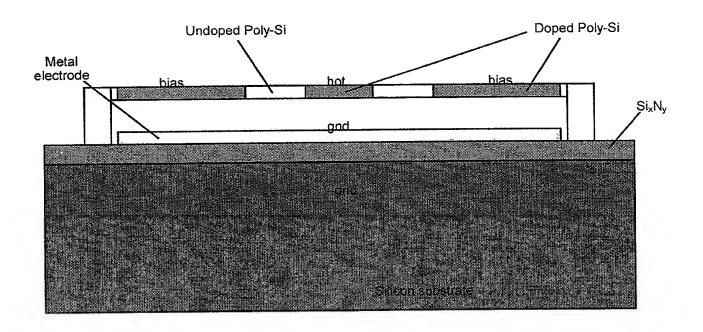


Fig. 9

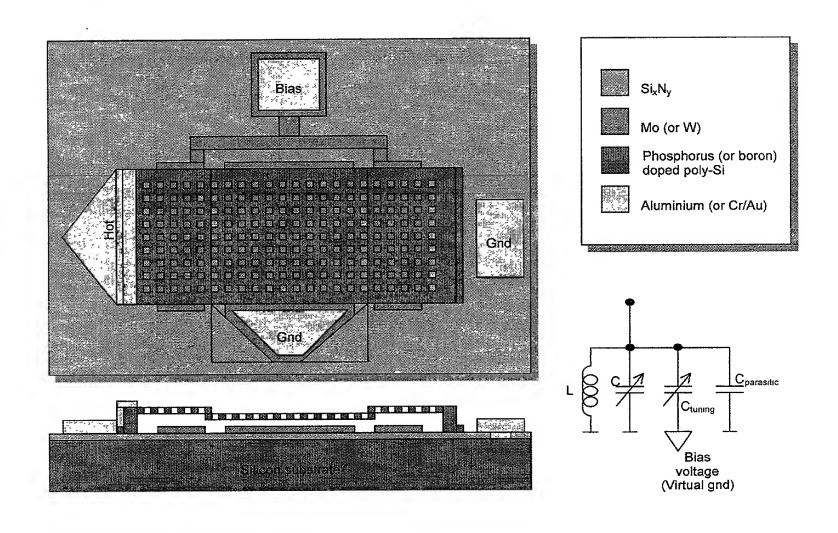
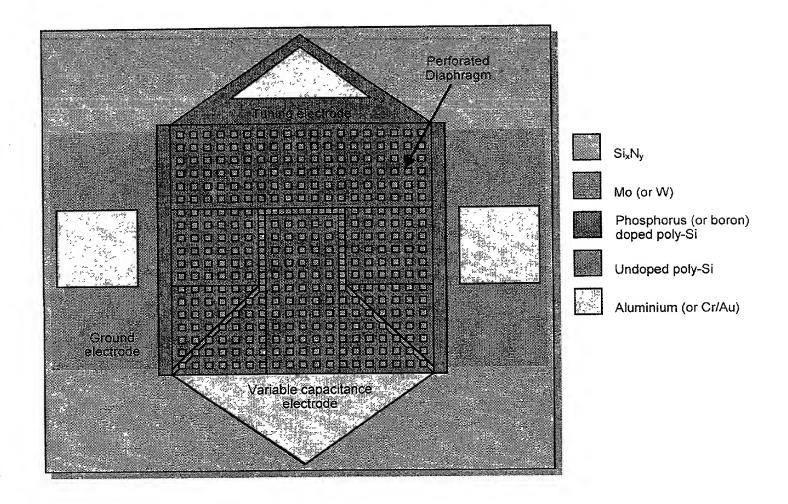


Fig. 10c



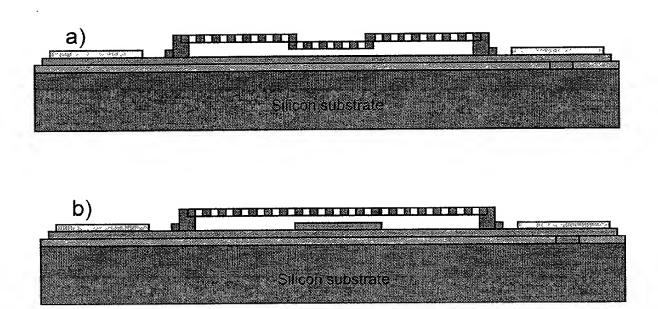


Fig. 10a,b

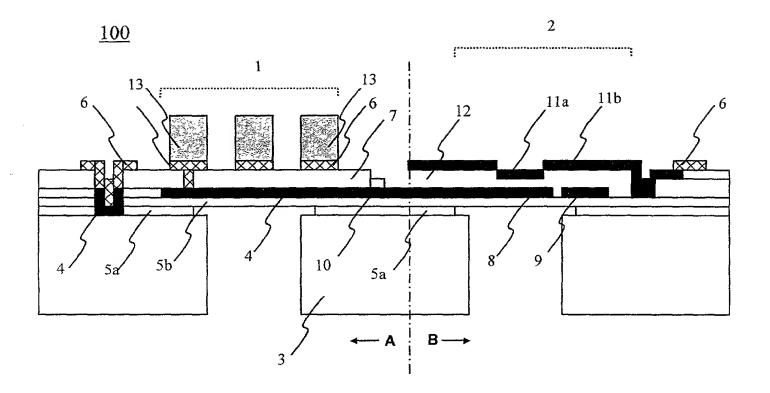


FIG. 11a

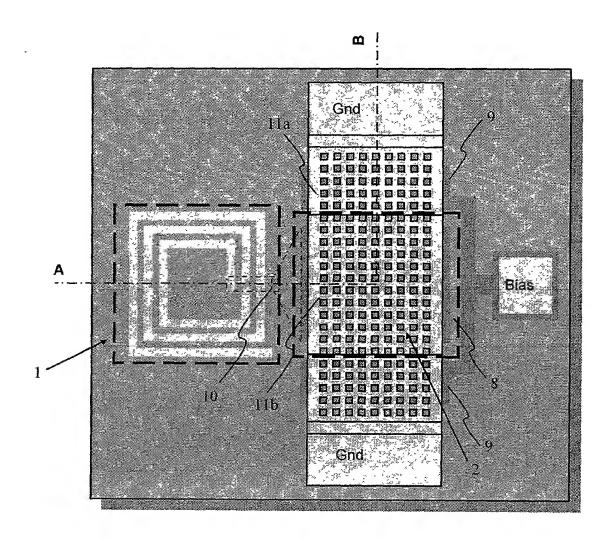


FIG. 11b

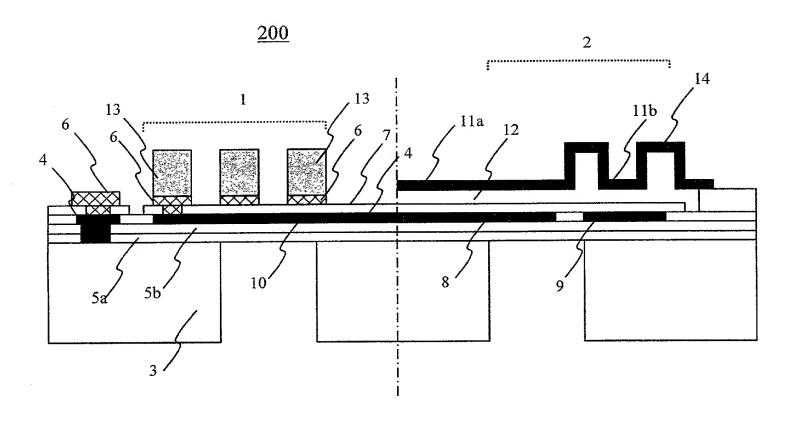


FIG. 12